# 1990 Index
# IEEE Transactions on Semiconductor Manufacturing
# Vol. 3

This index covers all items — papers, correspondence, reviews, etc. — that appeared in this periodical during 1990, and items from previous years that were commented upon or corrected in 1990.

The *Author Index* contains the primary entry for each item, listed under the first author's name, and cross-references from all coauthors. The *Subject Index* contains several entries for each item under appropriate subject headings, and subject cross-references.

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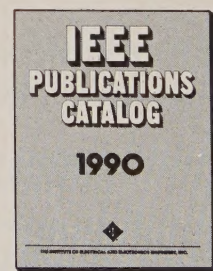
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